



TT030N065EI

主要参数 MAIN CHARACTERISTICS

I_c	30A
V_{CES}	650V
$V_{CE(sat)}$ -TYP	1.7V

用途

- 白电领域

APPLICATIONS

- White electricity field

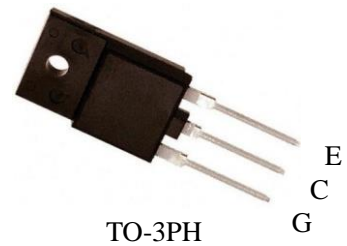
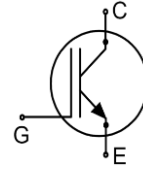
产品特性

- 低栅极电荷
- Trench FS 技术
- RoHS 产品
- 低 V_{CEsat}

FEATURES

- Low gate charge
- Trench FS Technology
- RoHS product
- Low V_{CEsat}

封装 Package



TO-3PH

订货信息 ORDER MESSAGE

订货型号 Order codes	印记 Marking	封装 Package
无卤-条管 Halogen-Free-Tube		
TT030N065EI-GA-BR	TT030N065EI	TO-3PH

绝对最大额定值 ABSOLUTE RATINGS ($T_C=25^{\circ}\text{C}$)

项 目 Parameter	符 号 Symbol	数 值 Value	单 位 Unit
最高集电极-发射极直流电压 Collector-emitter voltage	V_{CE}	650	V
*连续集电极电流 Collector current-continuous $T_C=25^{\circ}\text{C}$ $T_C=100^{\circ}\text{C}$	I_C	60 30	A
最大脉冲集电极极电流 Collector current – pulse ($p_w < 1\text{ms}$, duty cycle ≤ 0.01)	I_{CM}	120	A
栅极发射极电压 Gate-emitter voltage 瞬态栅极发射极电压 Transient gate-emitter voltage ($p_w \leq 10\mu\text{s}$, duty cycle < 0.01)	V_{GE}	± 20 ± 30	V
安全工作区 Turn-off safe area	-	120	A
耗散功率 Power dissipation $T_C=25^{\circ}\text{C}$ $T_C=100^{\circ}\text{C}$	P_D	71 35	W
存储温度 Storage temperature range	T_{STG}	$-55 \sim +150$	$^{\circ}\text{C}$
结温 Junction temperature range	T_{VJ}	$-40 \sim +175$	$^{\circ}\text{C}$
引线最高焊接温度 Maximum lead temperature for soldering Purposes	T_L	300	$^{\circ}\text{C}$
绝缘耐压 Isolation voltage	V_{ISO}	1500	V

*连续集电极电流由最高结温限制

*Collector current limited by maximum junction temperature



电特性 ELECTRICAL CHARACTERISTICS

项 目 Parameter	符 号 Symbol	测试条件 Tests conditions	最小 Min	典型 Typ	最大 Max	单位 Units
关态特性 Off –Characteristics						
集电极-发射极击穿电压 Collector-emitter voltage	BV_{CES}	$I_C=250\mu A, V_{GE}=0V$	650	-	-	V
零栅压下集电极漏电流 Zero gate voltage collector current	I_{CES}	$V_{CE}=650V, V_{GE}=0V, T_C=25^\circ C$	-	-	100	μA
		$V_{CE}=650V, V_{GE}=0V, T_C=175^\circ C$	-	1.0	-	mA
正向栅极体漏电流 Gate-body leakage current,forward	I_{GESF}	$V_{CE}=0V, V_{GE}=20V$	-	-	200	nA
反向栅极体漏电流 Gate-body leakage current,reverse	I_{GESR}	$V_{CE}=0V, V_{GE}=-20V$	-	-	-200	nA
通态特性 On-Characteristics						
阈值电压 Gate threshold voltage	$V_{GE(th)}$	$V_{CE}=V_{GE}, I_C=250\mu A$	4.5	-	6.5	V
饱和压降 Collector-emitter saturation voltage	V_{CESAT}	$V_{GE}=15V, I_C=30A, T_C=25^\circ C$	-	1.7	2.1	V
		$V_{GE}=15V, I_C=30A, T_C=125^\circ C$	-	1.8	-	V
		$V_{GE}=15V, I_C=30A, T_C=175^\circ C$	-	2.0	-	V
动态特性 Dynamic Characteristics						
输入电容 Input capacitance	C_{ies}	$V_{CE}=25V, V_{GE}=0V, f=1.0MHz$	-	1830	-	pF
输出电容 Output capacitance	C_{oes}		-	160	-	pF
反向传输电容 Reverse transfer capacitance	C_{res}		-	50.3	-	pF
栅极电荷总量 Total gate charge	Q_g	$V_{CC}=520V, I_C=30A, R_g=7.9\Omega, V_{GE}=15V, T_C=25^\circ C$	-	64.5	-	nC
栅极-发射极 Gate to emitter charge	Q_{ge}		-	18.1	-	
栅极-集电极 Gate to collector charge	Q_{gc}		-	23.7	-	
栅极电阻 Gate resistance	R_g	$f=1MHz, \text{open collector}$	-	1.1	-	Ω
短路电流 Short current	I_{sc}	$V_{GE}=15V, V_{CE}=300V, t \leq 10\mu s$	-	150	-	A





电特性 ELECTRICAL CHARACTERISTICS

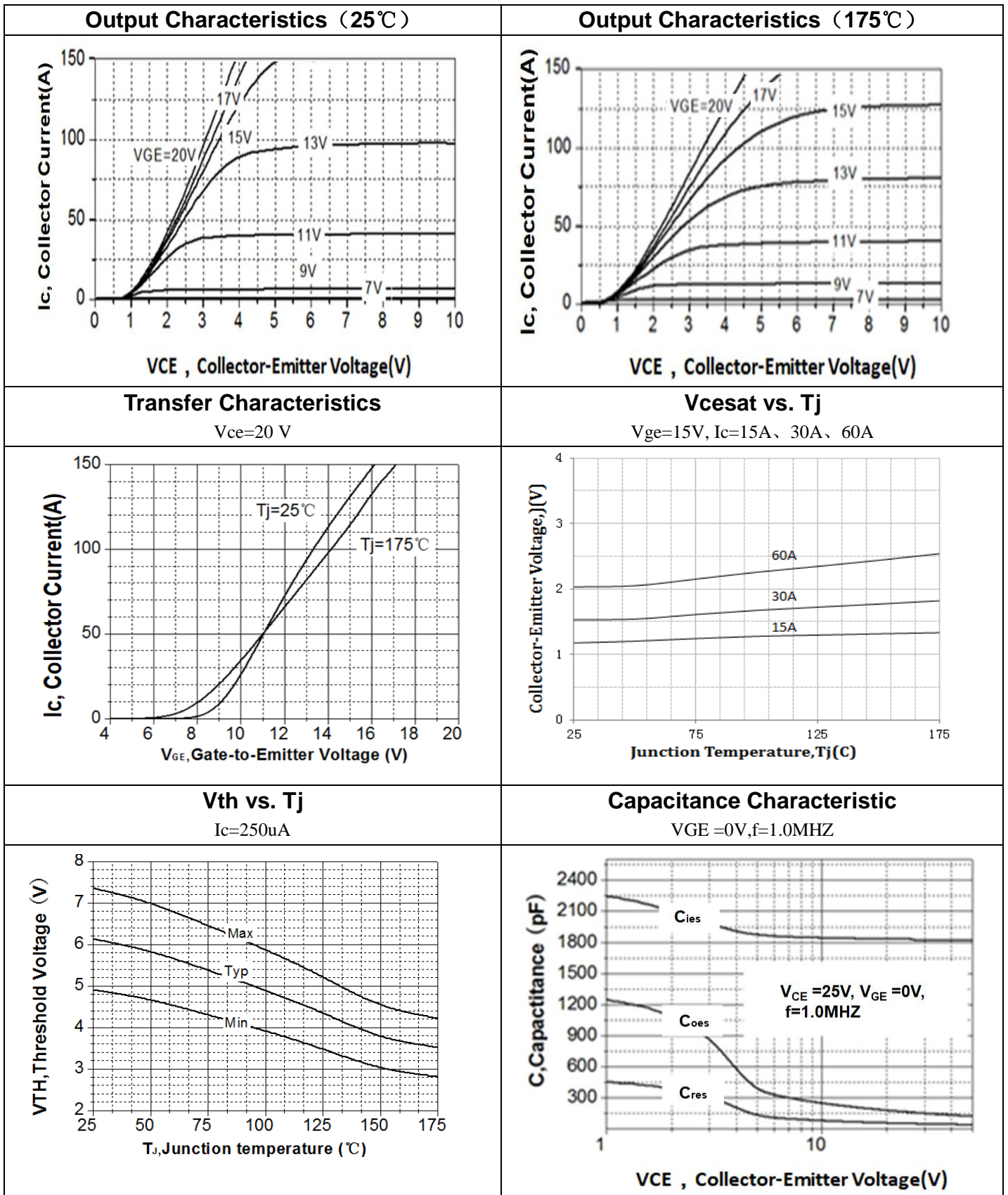
开关特性 Switching Characteristics

项 目 Parameter	符 号 Symbol	测试条件 Tests conditions	最小 Min	典型 Typ	最大 Max	单位 Units	
开启延迟时间 Turn-on delay time	td(on)	V _{CC} =400V, I _C =30A, R _g =7.9Ω V _{GE} =15 V T _c =25°C	-	27.0	-	ns	
上升时间 Turn-on rise time	tr		-	67.0	-	ns	
关断延迟时间 Turn-off delay time	td(off)		-	67.0	-	ns	
下降时间 Turn-off fall time	tf		-	44.0	-	ns	
开通损耗 Turn-on energy	E _{on}		-	0.83	-	mJ	
关断损耗 Turn-off energy	E _{off}		-	0.36	-	mJ	
总开关损耗 Total switching energy	E _{tot}		-	1.19	-	mJ	
开启延迟时间 Turn-on delay time	td(on)		V _{CC} =400V, I _C =30A, R _g =7.9Ω V _{GE} =15 V T _c =175°C	-	27.0	-	ns
上升时间 Turn-on rise time	tr			-	68.0	-	ns
关断延迟时间 Turn-off delay time	td(off)			-	90.0	-	ns
下降时间 Turn-off fall time	tf			-	59.0	-	ns
开通损耗 Turn-on energy	E _{on}				1.09		mJ
关断损耗 Turn-off energy	E _{off}			0.58		mJ	
总开关损耗 Total switching energy	E _{tot}			1.67		mJ	
关断电压变化率 Turn-off dv/dt	dv/dt	V _{CC} =400V, I _C =30A, R _g =10Ω V _{GE} =15 V, T _c =25°C		6140		V/us	

项 目 Parameter	符 号 Symbol	Typ	Max	单 位 Unit
IGBT 结到管壳的热阻 IGBT thermal resistance, Junction -case	R _{th(j-c)}	1.86	2.1	°C/W

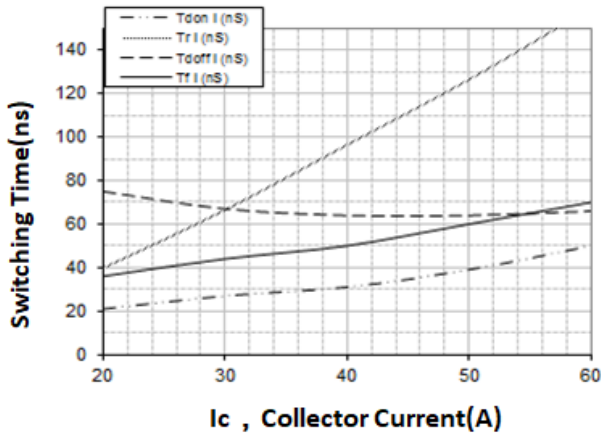


特征曲线 ELECTRICAL CHARACTERISTICS (curves)

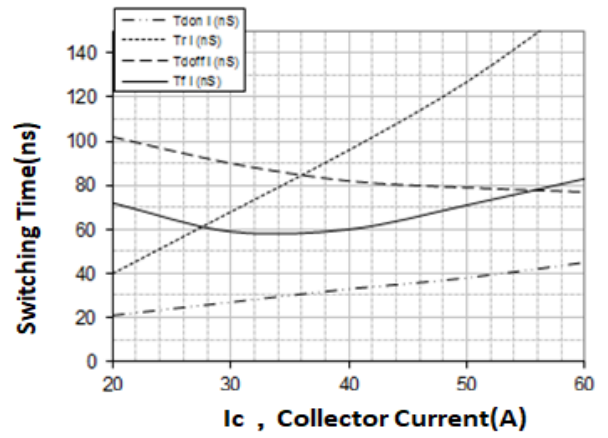




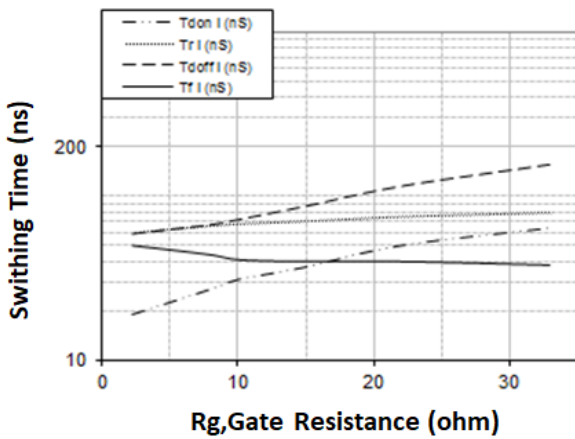
Switching Time vs. Ic(25°C)
VCE=400V, VGE=15V, RG=7.9Ω



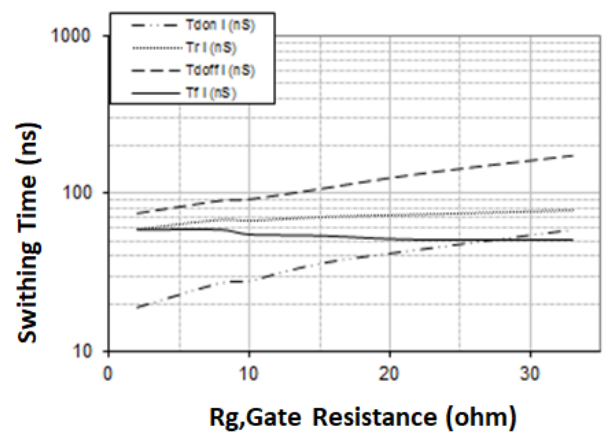
Switching Time vs. Ic(175°C)
VCE=400V, VGE=15V, RG=7.9Ω



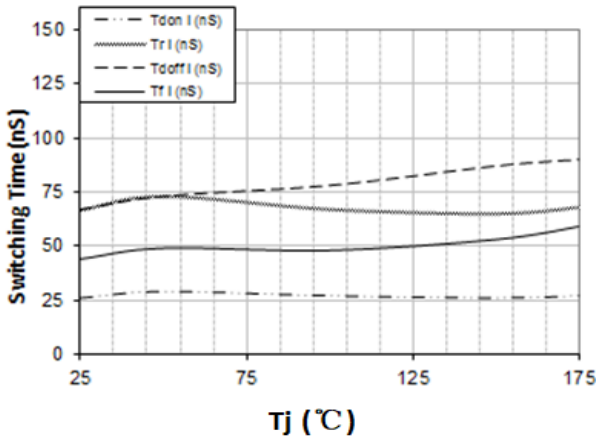
Switching Time vs. Rg(25°C)
VGE=15V, VCE=400V, IC=30A



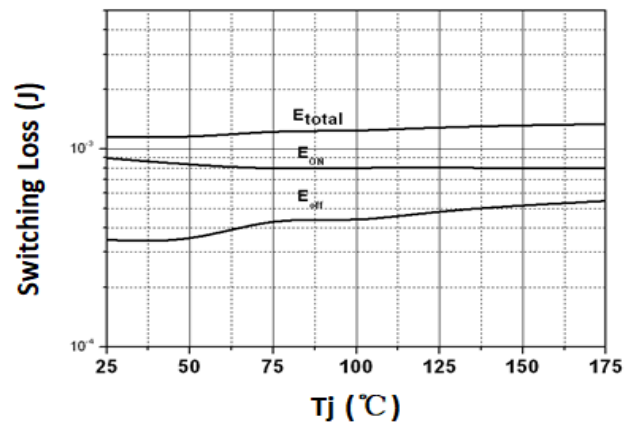
Switching Time vs. Rg(175°C)
VGE=15V, VCE=400V, IC=30A



Switching Time vs. Tj
VGE=15V, VCE=400V, IC=30A, RG=7.9Ω



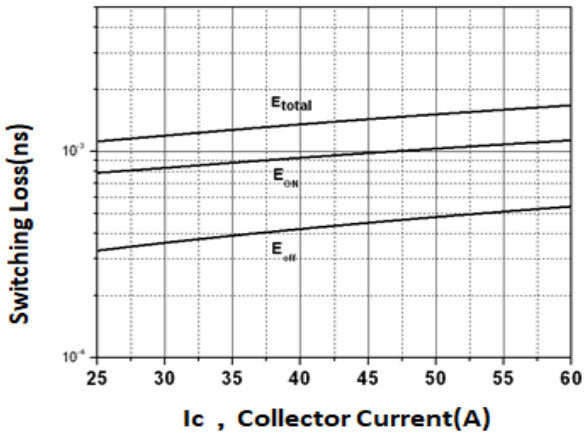
Switching Loss vs. Tj
VGE=15V, VCE=400V, IC=30A, RG=7.9Ω





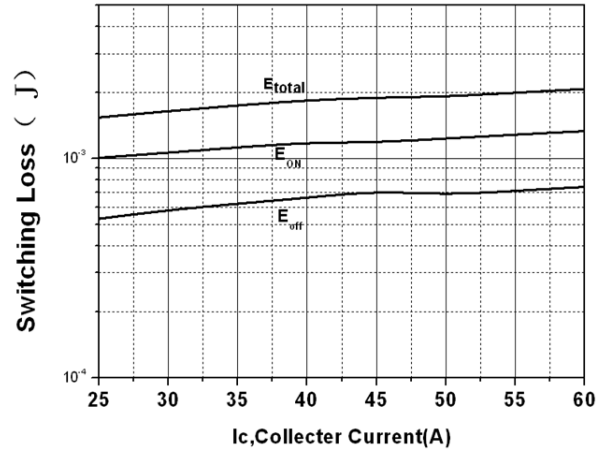
Switching Loss vs. Ic(25°C)

VGE=15V, VCE=400V, RG=7.9Ω



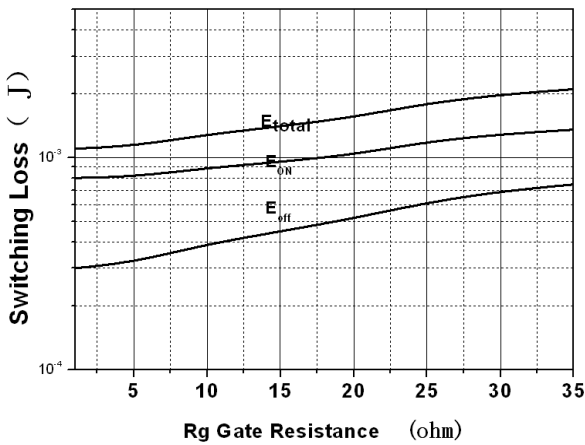
Switching Loss vs. Ic(175°C)

VGE=15V, VCE=400V, RG=7.9Ω



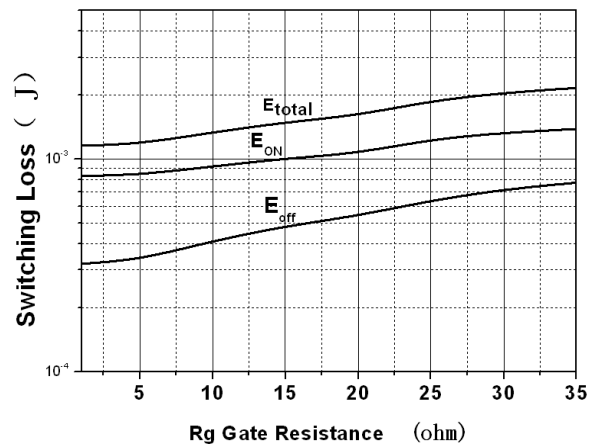
Switching Loss vs. Rg(25°C)

VGE=15V, VCE=400V, IC=30A



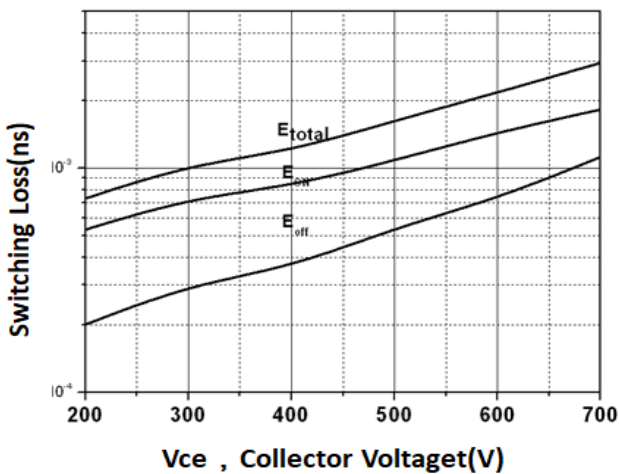
Switching Loss vs. Rg(175°C)

VGE=15V, VCE=400V, IC=30A



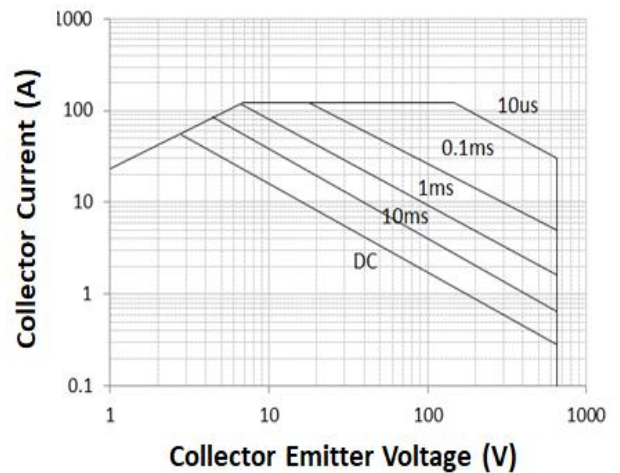
Switching Loss vs. VCE(175°C)

VGE=15V, IC=30A, RG=7.9Ω



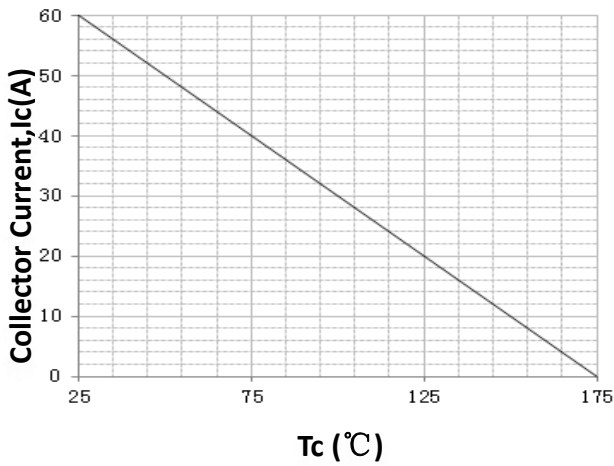
Forward Bias Safe Operating Area

Tc=25 °C, VGE=15V, Tvj ≤ 150 °C

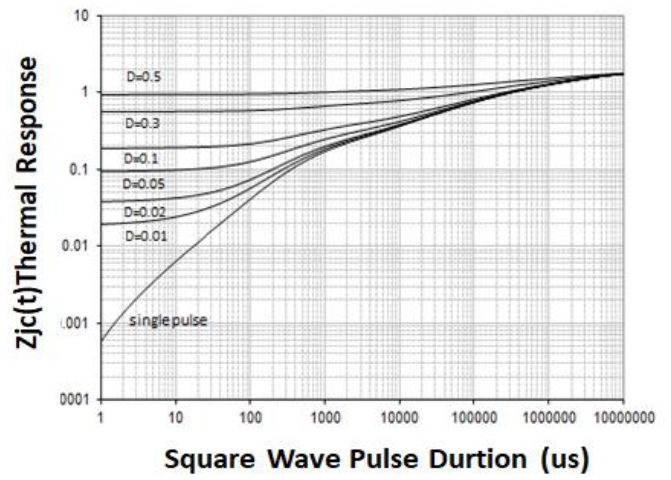




Ic vs.Tc

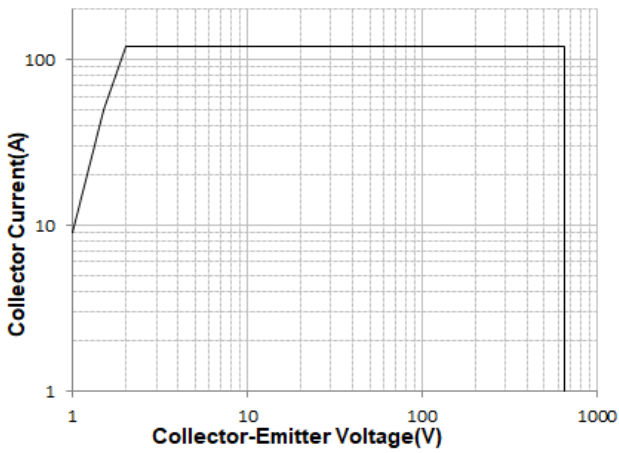


Transient Thermal Impedance

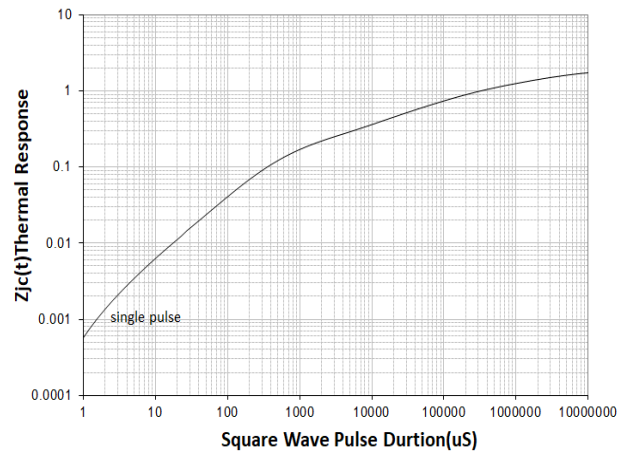


Reverse Bias Safe Operating Area

Tc=25 °C, VGE=±15V, Rg=10 Ω, Tvj≤150°C



Transient Thermal Impedance

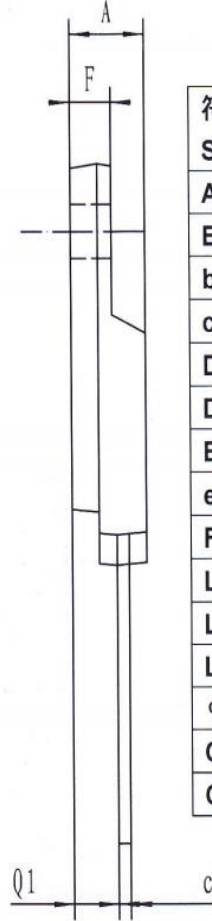
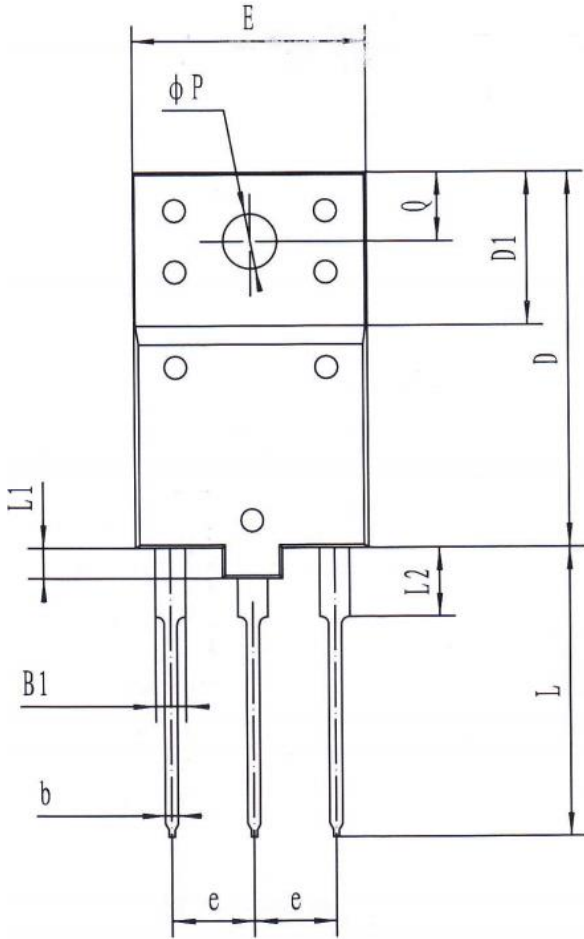




外形尺寸 PACKAGE MECHANICAL DATA

TO-3PH

单位 Unit: mm



符号 Symbol	Min	Max
A	5.2	5.8
B1	1.8	2.2
b	0.75	1.05
c	0.8	1.1
D	24.0	25.0
D1	9.8	10.2
E	15.0	16.0
e	5.45 (typ)	
F	2.7	3.3
L	18.5	19.5
L1	1.8	2.2
L2	4.3	4.7
ϕP	3.4	3.8
Q	4.3	4.7
Q1	3.1	3.5

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